

FORM 1449*

INFORMATION DISCLOSURE STATEMENT

IN AN APPLICATION

(Use several sheets if necessary)

Docket Number:

510015-265

Application Number:

09/935,012

Applicant: Larry A. Coldren et al.

Filing Date: August 21, 2001

Group Art Unit: 2881

U.S. PATENT DOCUMENTS

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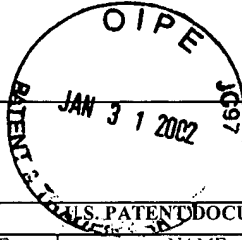
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| FORM 1449* INFORMATION DISCLOSURE STATEMENT IN AN APPLICATION (Use several sheets if necessary) | Docket Number: 510015-265 | Application Number: 09/935,012 |
| | Applicant: Larry A. Coldren et al. | |
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| Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary) | | | | Complete if Known | |
| | | | | Application Number | 09/935,012 |
| | | | | Filing Date | August 21, 2001 |
| | | | | First Named Inventor | Larry A. Coldren et al. |
| | | | | Art Unit | 2881 |
| | | | | Examiner Name | Not assigned |
| Sheet | 1 | of | 1 | Attorney Docket Number | 510015-265 |

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| Examiner Signature | Delma R. Flores Ruiz | Date Considered | 11/02 |
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